

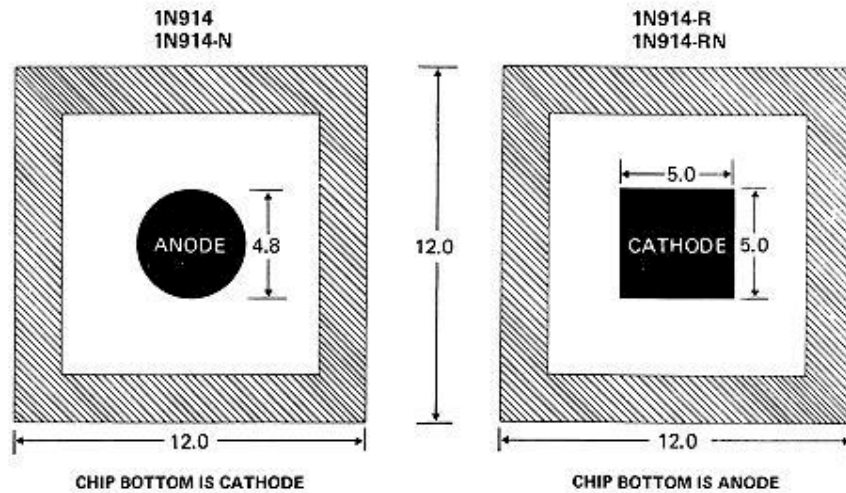
# DIONICS INC.

65 RUSHMORE ST., WESTBURY, N.Y. 11590 516-937-7474



1N914  
1N914-N  
1N914-R  
1N914-RN  
1N914-B

COMPLEMENTARY SWITCHING DIODE CHIPS  
FOR HYBRID CIRCUIT APPLICATIONS



ALL DIMENSIONS IN MILS.



- Chip Thickness = 6.0 Mils  $\pm$  1 Mil
- Distance from Bonding Pad to edge of Chip = 3.0 Mils

Detailed Specifications on Reverse Side

# DIONICS INC.

65 RUSHMORE ST., WESTBURY, N. Y. 11590 516-997-7474



1N914  
1N914-N  
1N914-R  
1N914-RN  
1N914-B

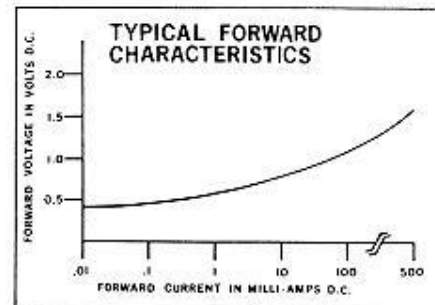
\*EQUIVALENT TO 1N4148

COMPLEMENTARY SWITCHING DIODE CHIPS  
FOR HYBRID CIRCUIT APPLICATIONS

- Complementary Construction • Fast Switching • Low Leakage
- Available in Chip, Array, or Slice Form

For use in hybrid circuit applications, the Dionics 1N914 Series of Complementary Switching Diode Chips afford the circuit designer a new degree of versatility. The 1N914 is a conventional P on N type device while the 1N914-R is the reverse N on P type. Both are gold-doped, fast switching units and have different bonding pad geometries for identification purposes. The N-versions of each, 1N914-N and 1N914-RN, are non-gold doped, slower switching devices with superior leakage current characteristics. When die-bonded as complementary chips on the same substrate conductor, they simplify the problem of series stacking as anodes and cathodes form a common connection. The 1N914-B is a higher current version of the 1N914.

All versions may be scribed as monolithic diode arrays in either the common cathode or common anode configuration. Chips are gold backed for eutectic die-attach and have aluminum bonding pads for all conventional wire bonding techniques.



← 100% Probe Tested to These Parameters @ 25°C → Guaranteed (tested on sample basis)

$V_{RR}$ Volts Min. @ $I_R=100\mu A$	$I_F$ $\mu A$ Max. @ $V_F$ Volts	$I_S$ $\mu A$ Max. @ $V_R$ Volts	$I_R$ mA Min. @ $V_R=1.0V$	$C_T$ pf Max. @ 0 V	$t_r$ Max. in N-Sec @ $I_F=10mA$ ; recover to $I_F=1 mA$
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Device	$V_{RR}$ (Volts Min. @ $I_R=100\mu A$ )	$I_F$ ( $\mu A$ Max. @ $V_F$ Volts)	$I_S$ ( $\mu A$ Max. @ $V_R$ Volts)	$I_R$ (mA Min. @ $V_R=1.0V$ )	$C_T$ (pf Max. @ 0 V)	$t_r$ (Max. in N-Sec @ $I_F=10mA$ ; recover to $I_F=1 mA$ )
1N914	100	5.0 @ 75V	0.025 @ 20V	10	4.0	4.0
1N914-B	75	5.0 @ 60V	0.025 @ 20V	50	4.0	4.0
1N914-N	100	1.0 @ 75V	0.001 @ 20V	10	4.0	100
1N914-R	60	5.0 @ 50V	0.025 @ 20V	10	6.0	50
1N914-RN	60	1.0 @ 50V	0.001 @ 20V	10	6.0	500

Dimensional Drawing on Reverse Side